

# MA3D756

Silicon epitaxial planar type (cathode common)

For switching power supply

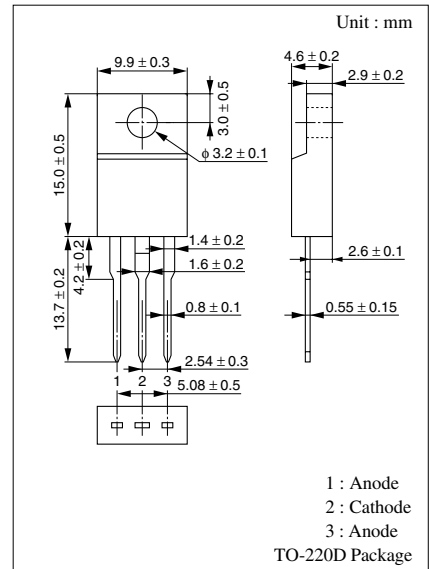
## ■ Features

- Low forward rise voltage  $V_F$
- TO-220D (Full-pack package) with high dielectric breakdown voltage  $> 5.0$  kV
- Easy-to-mount, caused by its V cut lead end

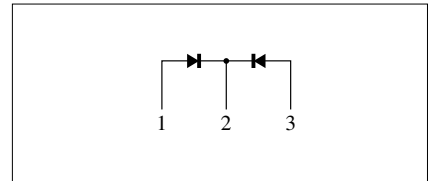
## ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Repetitive peak reverse voltage	$V_{RRM}$	60	V
Average forward current	$I_{F(AV)}$	10	A
Non-repetitive peak forward surge current*	$I_{FSM}$	120	A
Junction temperature	$T_j$	-40 to +125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-40 to +125	$^\circ\text{C}$

Note) \* : Half sine-wave; 10 ms/cycle



## Internal Connection



## ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 60$ V			3	mA
Forward voltage (DC)	$V_F$	$I_F = 5$ A			0.58	V
Thermal resistance	$R_{th(j-c)}$	Direct current (between junction and case)			3	$^\circ\text{C/W}$

Note) Rated input/output frequency: 150 MHz

